MY3P10BF

-100V P-Channel Enhancement ModeMOSFET

MAOYUANWEI semiconductor

General Description

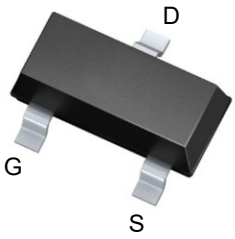
The MY3P10BF is the high cell density trenched P-CH MOSFET,which provide excellent $R_{DS(ON)}$ and efficiency for most of the small power switching and load s witch applications.

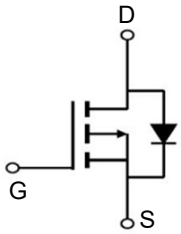
Features

V_{DSS}	-100	V
I_D	-2.9	A
$R_{DS(ON)}$(atV_{GS}=-10V)	0.54	mΩ
$R_{DS(ON)}$(atV_{GS}=-4.5V)	0.57	mΩ

Application

- Battery protection
- Load switch
- Uninterruptible power supply





Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY3P10BF	SOT-23	3P10	3000

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain- Source Voltage	-100	V
VGS	Gate- Source Voltage	±20	V
I_D@T_A=25℃	Drain Current[3] , V_{GS} @ 10V	-2.9	A
I_D@T_A=70℃	Drain Current[3] , V_{GS} @ 10V	-2.7	A
IDM	Pulsed Drain Current[1]	-1.8	A
P_D@T_A=25℃	Total Power Dissipation	1	W
TSTG	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
Rthj-c	Maximum Thermal Resistance, Junction- case	80	℃/W
Rthj-a	Maximum Thermal Resistance, Junction- ambient[3]	125	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-100	---	---	V
△BVDSS/△TJ	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.0624	---	V/℃
RDS(ON)	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-0.8A	---	0.54	0.65	Ω
		V_{GS}=-4.5V , I_D=-0.4A	---	0.57	0.7	
VGS(th)	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.0	-1.5	-2.5	V
△$V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.5	---	mV/℃
IDSS	Drain-Source Leakage Current	V_{DS}=-80V , V_{GS}=0V , T_J=25℃	---	---	10	uA
		V_{DS}=-80V , V_{GS}=0V , T_J=55℃	---	---	100	
IGSS	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-0.8A	---	3	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	16	32	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-15V , V_{GS}=-4.5V , I_D=-0.5A	---	4.5	---	nC
Qgs	Gate-Source Charge		---	1.14	---	
Qgd	Gate-Drain Charge		---	1.5	---	
Td(on)	Turn-On Delay Time	V_{DD}=-50V , V_{GS}=-10V , R_G=3.3□ I_D=-0.5A	---	13.6	---	ns
T_r	Rise Time		---	6.8	---	
Td(off)	Turn-Off Delay Time		---	34	---	
T_f	Fall Time		---	3	---	
Ciss	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	445.5	---	pF
Coss	Output Capacitance		---	22.7	---	
Crss	Reverse Transfer Capacitance		---	20	---	
IS	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	-0.9	A
ISM	Pulsed Source Current[2,4]		---	---	-1.8	A
VSD	Diode Forward Voltage[2]	V_{GS}=0V , Is=-1A , T_J=25℃	---	---	-1.2	V

Note :

1.The data tested by surface mounted on a 1 inch²FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3.The power dissipation is limited by 150℃ junction temperature

4 .The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Switching Time Test Circuit and Waveforms

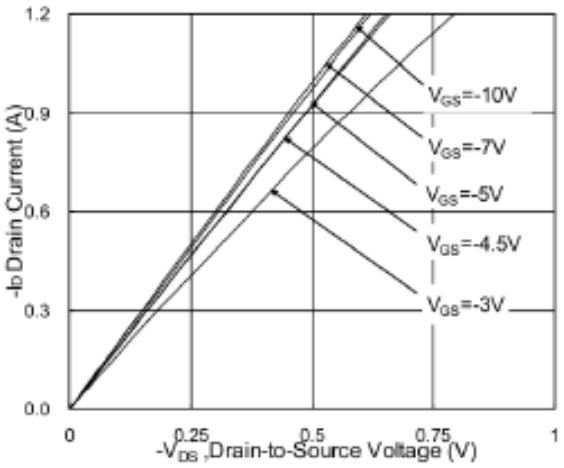


Fig.1 Typical Output Characteristics

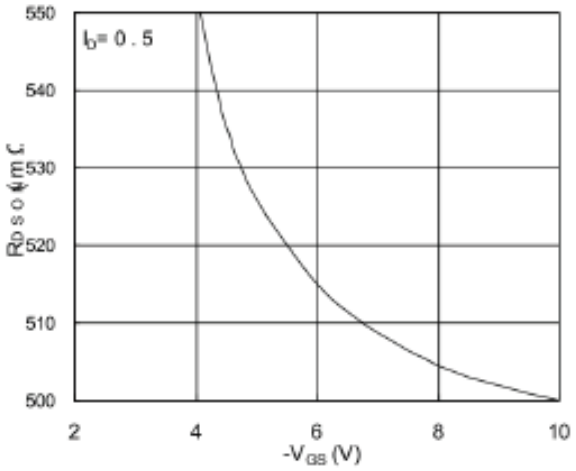


Fig.2 On-Resistance vs. Gate-Source

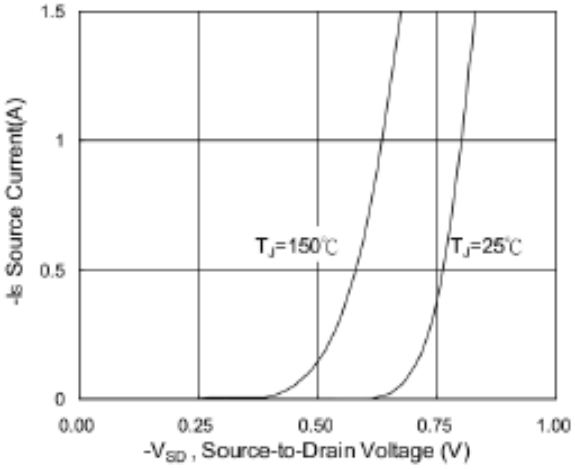


Fig.3 Forward Characteristics Of Reverse

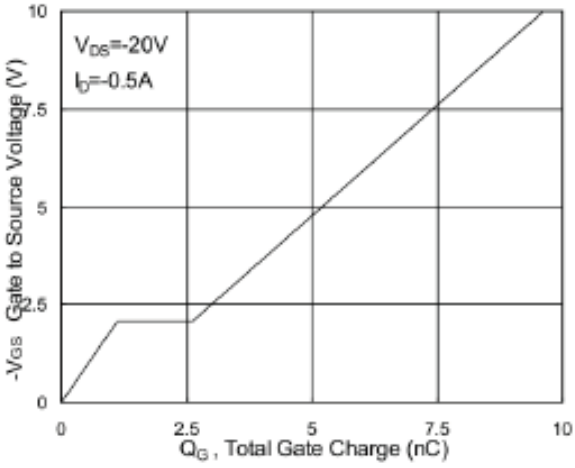


Fig.4 Gate-Charge Characteristics

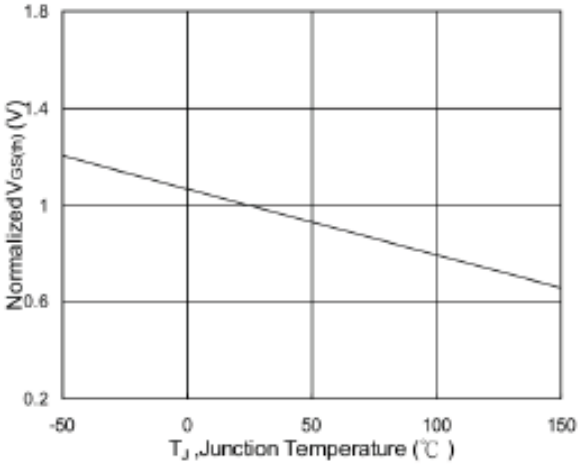


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

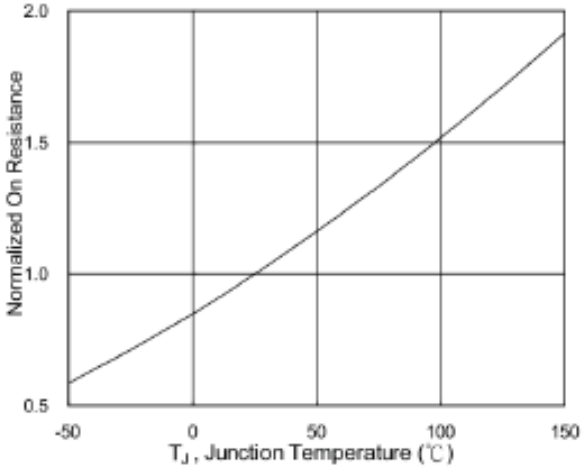


Fig.6 Normalized R_{DSON} vs. T_J

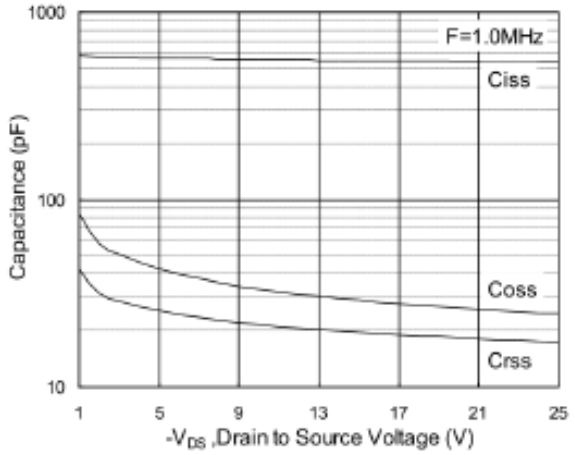


Fig.7 Capacitance

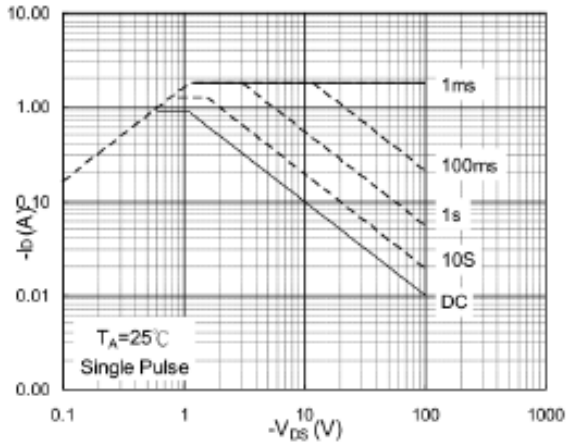


Fig.8 Safe Operating Area

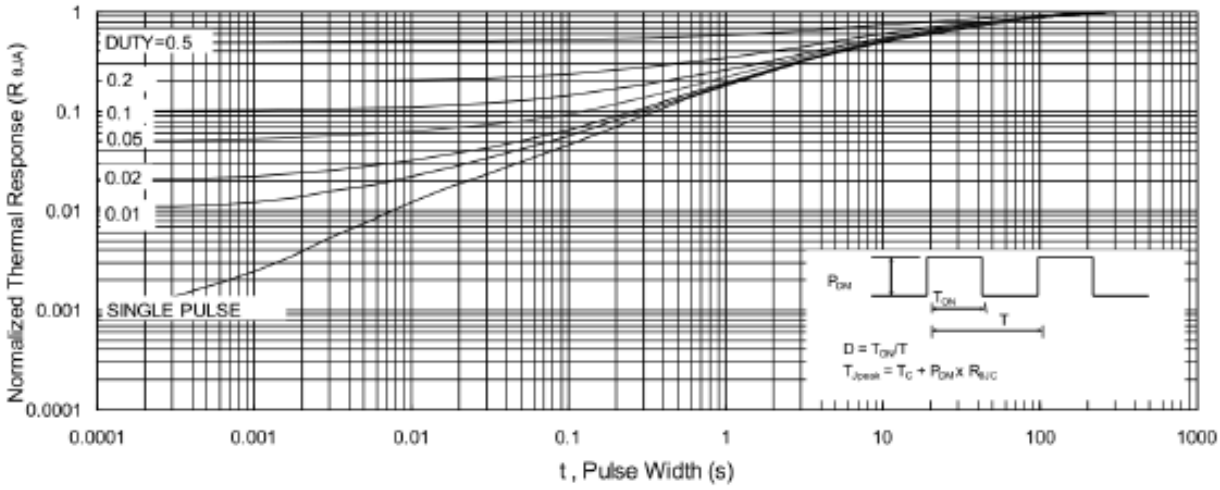


Fig.9 Normalized Maximum Transient Thermal Impedance

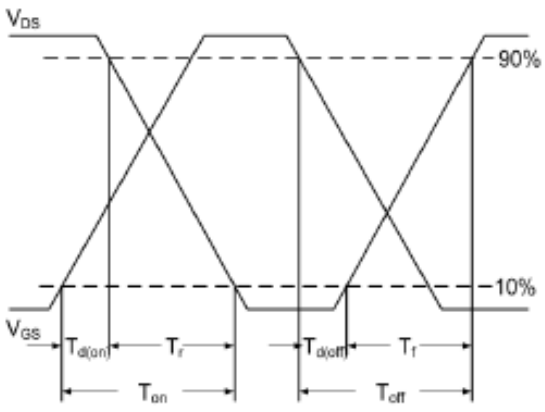


Fig.10 Switching Time Waveform

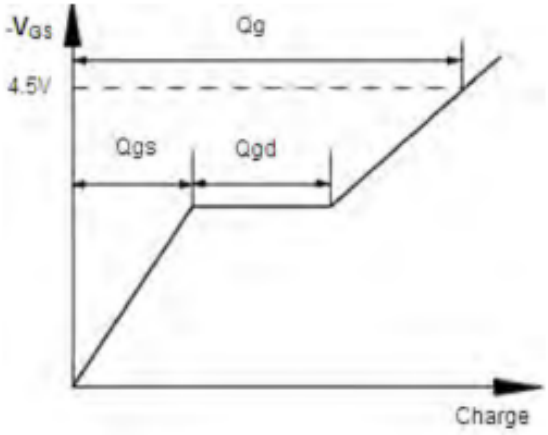
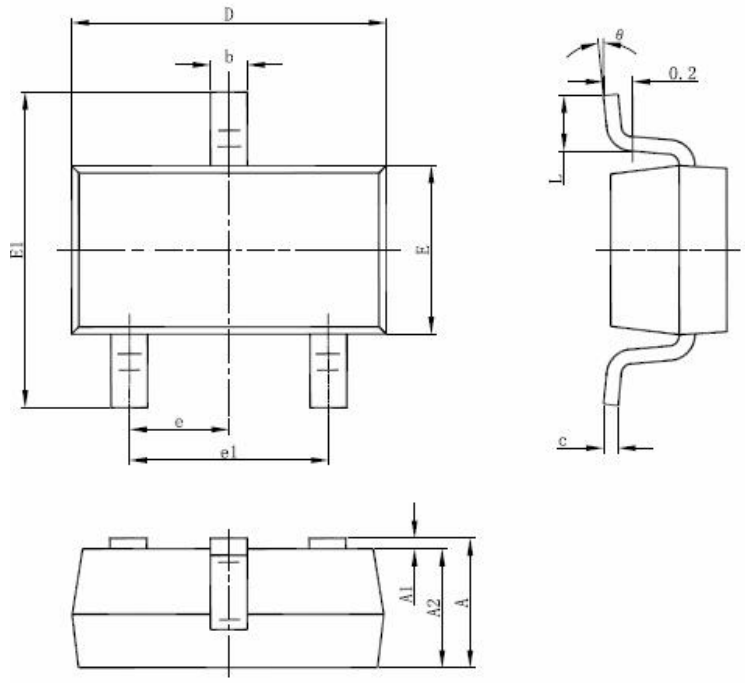


Fig.11 Gate Charge Waveform

Package Mechanical Data-SOT-23



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°